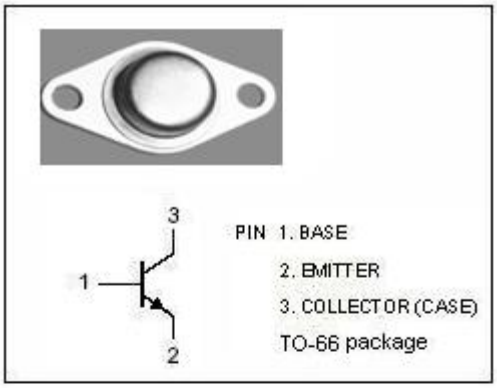
isc Silicon NPN Power Transistor — 2SC1034

DESCRIPTION

- DC Current Gain -h_{FE} = 4(Min)@ I_C= 0.75A
- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$ = 700V(Min)
- Minimum Lot-to-Lot variations for robust device performance and reliable operation.



APPLICATIONS

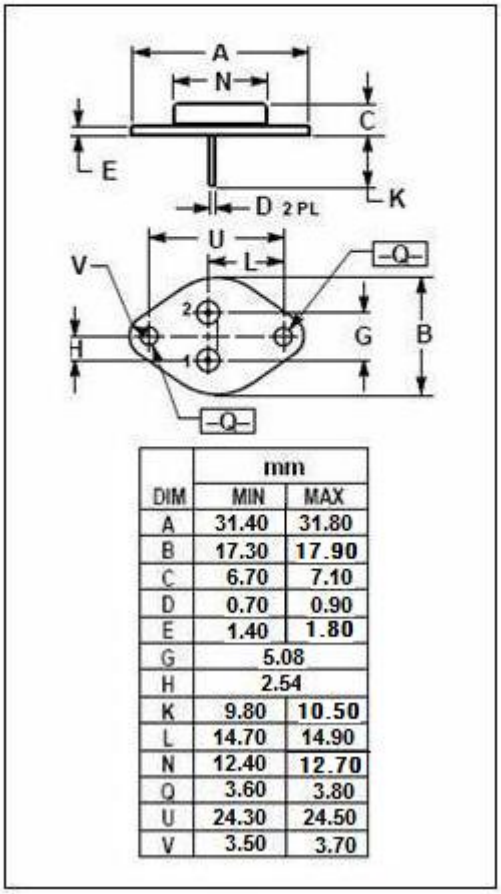
- Designed for use in general purpose power amplifier and switching applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1100	V
V_{CEO}	Collector-Emitter Voltage	700	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	1.0	A
I_{CM}	Collector Current-Peak	5.0	A
P_C	Collector Power Dissipation @ T_C=25℃	25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	5.0	℃/W



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.90
C	6.70	7.10
D	0.70	0.90
E	1.40	1.80
G	5.08	
H	2.54	
K	9.80	10.50
L	14.70	14.90
N	12.40	12.70
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 0.75A; I_B= 0.075A		5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 0.75A; I_B= 0.075A		1.4	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 800V;I_B= 0		5.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 8V; I_C=0		4.0	mA
h_{FE}	DC Current Gain	I_C= 0.75A ; V_{CE}= 3V	4	40	
f_T	Current-Gain—Bandwidth Product	I_C= 0.2A ; V_{CE}= 10V, f_{test}= 1.0MHz	5		MHz